

Input capacitance	Ciss	f = 1MHz V _{DS} =25V	-	280	-	pF
Output capacitance	Coss		-	46	-	
Reverse transfer capacitance	Crss		-	25	-	
Total gate charge	Qg	V _{DD} = 25V I _D = 5A V _{GS} = 10V	-	5.3	-	nC
Gate - Source charge	Qgs		-	1.4	-	
Gate - Drain charge	Qgd		-	0.8	-	

P Channel Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = -250uA	-30			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = -250uA	-1.2		-2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = -30V, V _{GS} = 0V			-1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			100	nA
Static Drain-source On Resistance		V _{GS} = -10V, I _D = -6A				
		V _{GS} = -4.5V, I _D = -4A				
Forward Transconductance	g _{FS}	V _{DS} = -10V, I _D = -5A				

Dynamic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Gate Resistance	Rg	f = 1MHz		10		
Input capacitance	Ciss	f = 1MHz V _{DS} =25V	-	850	-	pF
Output capacitance	Coss		-	125	-	
Reverse transfer capacitance	Crss		-	115	-	
Total gate charge	Qg	V _{DD} = 25V I _D = 5A V _{GS} = 10V	-	12	-	nC
Gate - Source charge	Qgs		-	5	-	
Gate - Drain charge	Qgd		-	6	-	

P Channel characteristics curve

Fig.1 Power Dissipation Derating Curve

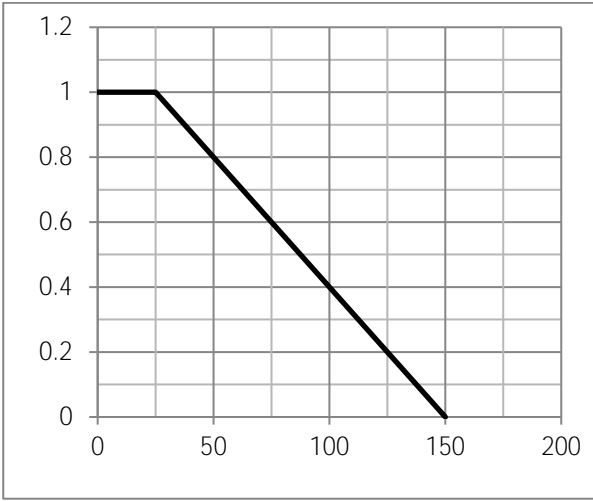


Fig.2 Typical output Characteristics

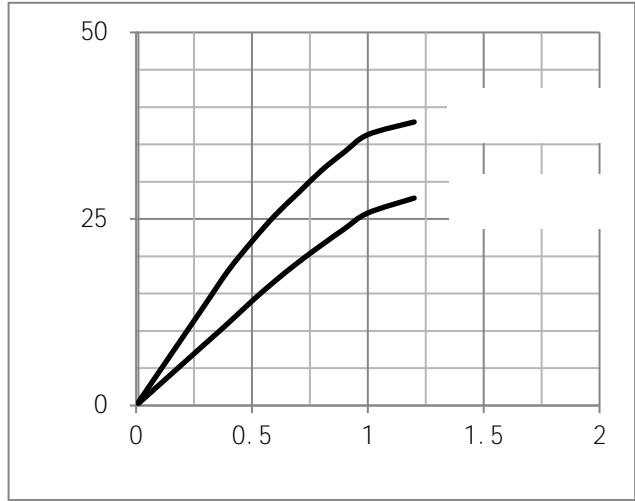


Fig.3 Threshold Voltage V.S Junction Temperature

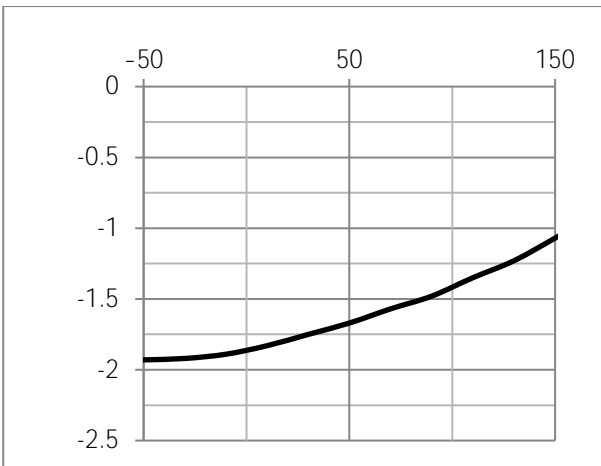
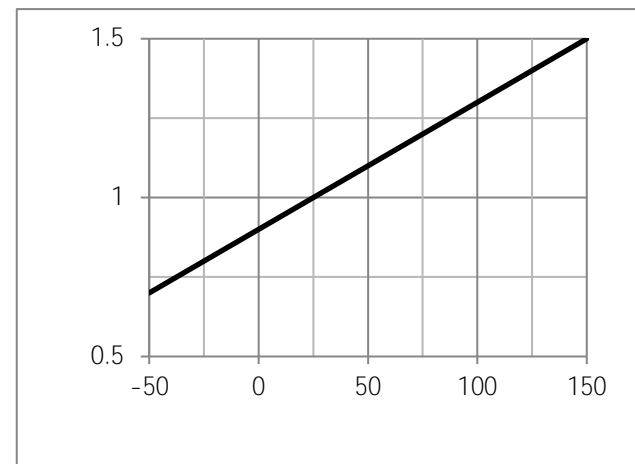
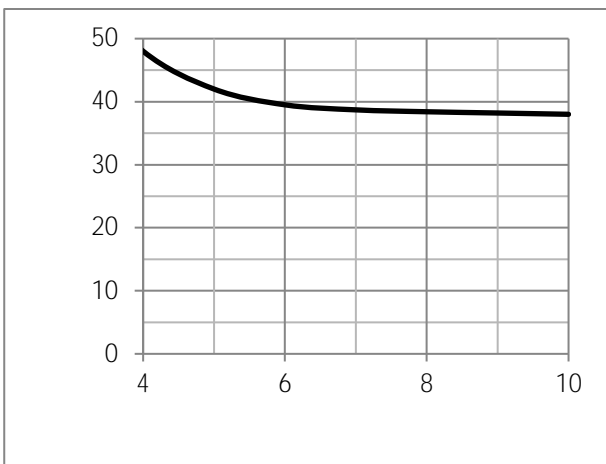
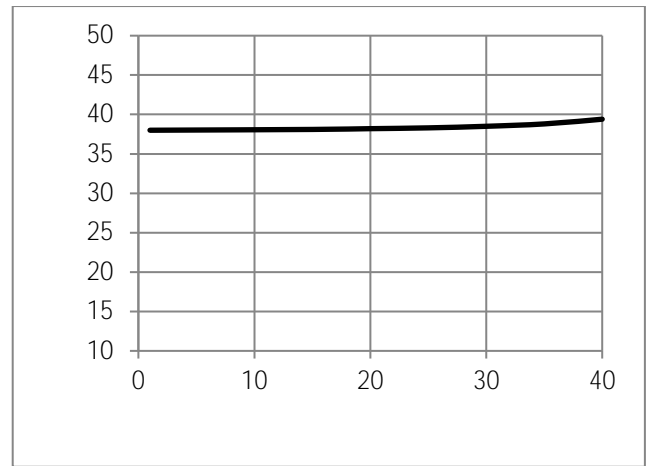


Fig.4 Resistance V.S Drain Current



Test Circuit

Fig.1 Switching Time Measurement Circuit

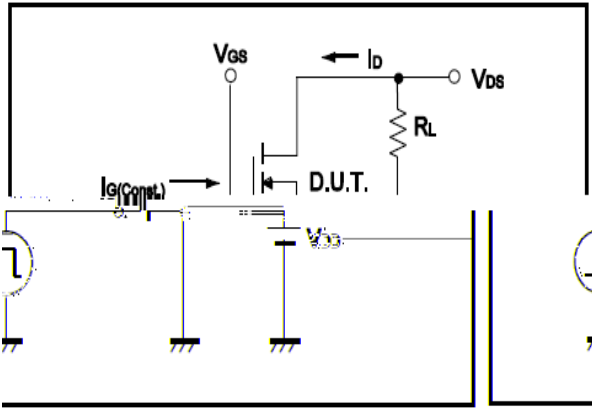


Fig.2 Gate Charge Waveform

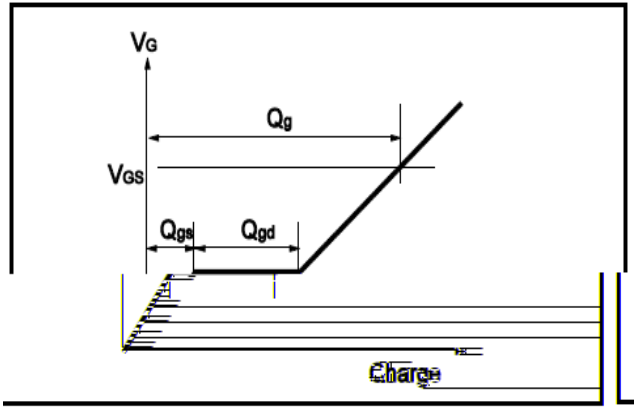


Fig.3 Switching Time Measurement Circuit

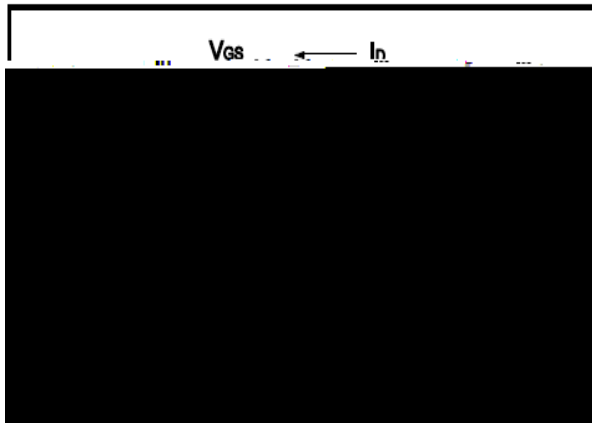


Fig.4 Gate Charge Waveform

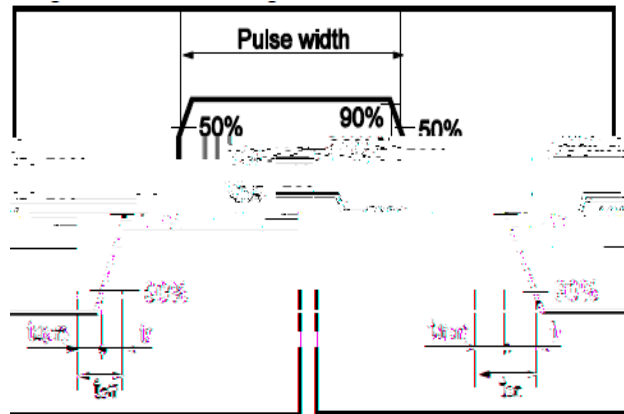


Fig.5 Avalanche Measurement Circuit

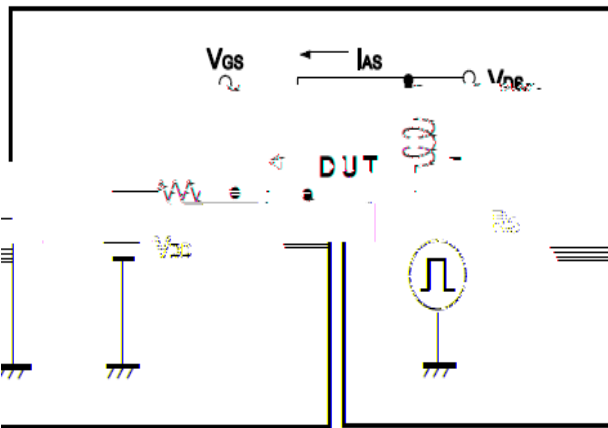
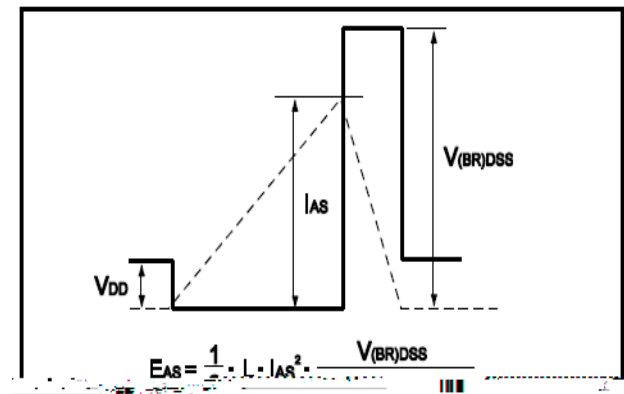


Fig.6 Avalanche Waveform





sions DFN5x6

Unit: mm

